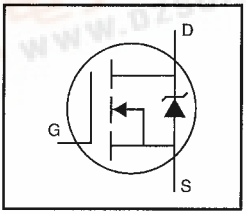
International Rectifier



# IRLR024
# IRLU024

HEXFET® Power MOSFET

- Dynamic dv/dt Rating
- Surface Mount (IRLR024)
- Straight Lead (IRLU024)
- Available in Tape & Reel
- Logic-Level Gate Drive
- $R_{DS(on)}$ Specified at $V_{GS}$=4V & 5V
- Fast Switching




$V_{DSS}$ = 60V

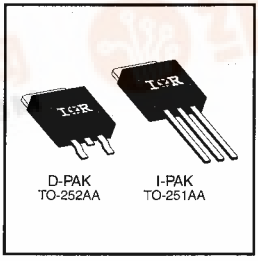
$R_{DS(on)}$ = 0.10Ω

$I_D$ = 14A

## Description

Third Generation HEXFETs from International Rectifier provide the designer with the best combination of fast switching, ruggedized device design, low on-resistance and cost-effectiveness.

The D-Pak is designed for surface mounting using vapor phase, infrared, or wave soldering techniques. The straight lead version (IRFU series) is for through-hole mounting applications. Power dissipation levels up to 1.5 watts are possible in typical surface mount applications.




DATA SHEETS

## Absolute Maximum Ratings

| | Parameter | Max. | Units |
|---|---|---|---|
| $I_D$ @ $T_C$ = 25°C | Continuous Drain Current, $V_{GS}$ @ 5.0 V | 14 | A |
| $I_D$ @ $T_C$ = 100°C | Continuous Drain Current, $V_{GS}$ @ 5.0 V | 9.2 | |
| $I_{DM}$ | Pulsed Drain Current ① | 56 | |
| $P_D$ @ $T_C$ = 25°C | Power Dissipation | 42 | W |
| $P_D$ @ $T_A$ = 25°C | Power Dissipation (PCB Mount)** | 2.5 | |
| | Linear Derating Factor | 0.33 | W/°C |
| | Linear Derating Factor (PCB Mount)** | 0.020 | |
| $V_{GS}$ | Gate-to-Source Voltage | ±10 | V |
| $E_{AS}$ | Single Pulse Avalanche Energy ② | 91 | mJ |
| dv/dt | Peak Diode Recovery dv/dt ③ | 4.5 | V/ns |
| $T_J$, $T_{STG}$ | Junction and Storage Temperature Range | -55 to +150 | °C |
| | Soldering Temperature, for 10 seconds | 260 (1.6mm from case) | |

## Thermal Resistance

| | Parameter | Min. | Typ. | Max. | Units |
|---|---|---|---|---|---|
| $R_{\theta JC}$ | Junction-to-Case | — | — | 3.0 | °C/W |
| $R_{\theta JA}$ | Junction-to-Ambient (PCB mount)** | — | — | 50 | |
| $R_{\theta JA}$ | Junction-to-Ambient | — | — | 110 | |

** When mounted on 1" square PCB (FR-4 or G-10 Material).

## Electrical Characteristics @ $T_J$ = 25°C (unless otherwise specified)

| | Parameter | Min. | Typ. | Max. | Units | Test Conditions |
|---|---|---|---|---|---|---|
| $V_{(BR)DSS}$ | Drain-to-Source Breakdown Voltage | 60 | — | — | V | $V_{GS}$=0V, $I_D$= 250μA |
| $\Delta V_{(BR)DSS}/\Delta T_J$ | Breakdown Voltage Temp. Coefficient | — | 0.068 | — | V/°C | Reference to 25°C, $I_D$= 1mA |
| $R_{DS(on)}$ | Static Drain-to-Source On-Resistance | — | — | 0.10 | Ω | $V_{GS}$=5.0V, $I_D$=8.4A ④ |
| | | — | — | 0.14 | | $V_{GS}$=4.0V, $I_D$=7.0A ④ |
| $V_{GS(th)}$ | Gate Threshold Voltage | 1.0 | — | 2.0 | V | $V_{DS}$=$V_{GS}$, $I_D$= 250μA |
| $g_{fs}$ | Forward Transconductance | 7.3 | — | — | S | $V_{DS}$=25V, $I_D$=8.4A ④ |
| $I_{DSS}$ | Drain-to-Source Leakage Current | — | — | 25 | μA | $V_{DS}$=60V, $V_{GS}$=0V |
| | | — | — | 250 | | $V_{DS}$=48V, $V_{GS}$=0V, $T_J$=125°C |
| $I_{GSS}$ | Gate-to-Source Forward Leakage | — | — | 100 | nA | $V_{GS}$=10V |
| | Gate-to-Source Reverse Leakage | — | — | -100 | | $V_{GS}$=-10V |
| $Q_g$ | Total Gate Charge | — | — | 18 | nC | $I_D$=17A |
| $Q_{gs}$ | Gate-to-Source Charge | — | — | 4.5 | | $V_{DS}$=48V |
| $Q_{gd}$ | Gate-to-Drain ("Miller") Charge | — | — | 12 | | $V_{GS}$=5.0V See Fig. 6 and 13 ④ |
| $t_{d(on)}$ | Turn-On Delay Time | — | 11 | — | ns | $V_{DD}$=30V |
| $t_r$ | Rise Time | — | 110 | — | | $I_D$=17A |
| $t_{d(off)}$ | Turn-Off Delay Time | — | 23 | — | | $R_G$=9.0Ω |
| $t_f$ | Fall Time | — | 41 | — | | $R_D$=1.7Ω See Figure 10 ④ |
| $L_D$ | Internal Drain Inductance | — | 4.5 | — | nH | Between lead, 6 mm (0.25in.) from package and center of die contact |
| $L_S$ | Internal Source Inductance | — | 7.5 | — | | |
| $C_{iss}$ | Input Capacitance | — | 870 | — | pF | $V_{GS}$=0V |
| $C_{oss}$ | Output Capacitance | — | 360 | — | | $V_{DS}$=25V |
| $C_{rss}$ | Reverse Transfer Capacitance | — | 53 | — | | $f$=1.0MHz See Figure 5 |

## Source-Drain Ratings and Characteristics

| | Parameter | Min. | Typ. | Max. | Units | Test Conditions |
|---|---|---|---|---|---|---|
| $I_S$ | Continuous Source Current (Body Diode) | — | — | 14 | A | MOSFET symbol showing the integral reverse p-n junction diode. |
| $I_{SM}$ | Pulsed Source Current (Body Diode) ① | — | — | 56 | | |
| $V_{SD}$ | Diode Forward Voltage | — | — | 1.5 | V | $T_J$=25°C, $I_S$=14A, $V_{GS}$=0V ④ |
| $t_{rr}$ | Reverse Recovery Time | — | 130 | 260 | ns | $T_J$=25°C, $I_F$=17A |
| $Q_{rr}$ | Reverse Recovery Charge | — | 0.75 | 1.5 | μC | di/dt=100A/μs ④ |
| $t_{on}$ | Forward Turn-On Time | Intrinsic turn-on time is neglegible (turn-on is dominated by $L_S$+$L_D$) | | | | |

Notes:

① Repetitive rating; pulse width limited by max. junction temperature (See Figure 11)

② $V_{DD}$=25V, starting $T_J$=25°C, L=541μH $R_G$=25Ω, $I_{AS}$=14A (See Figure 12)

③ $I_{SD}$≤17A, di/dt≤140A/μs, $V_{DD}$≤$V_{(BR)DSS}$, $T_J$≤150°C

④ Pulse width ≤ 300 μs; duty cycle ≤2%.

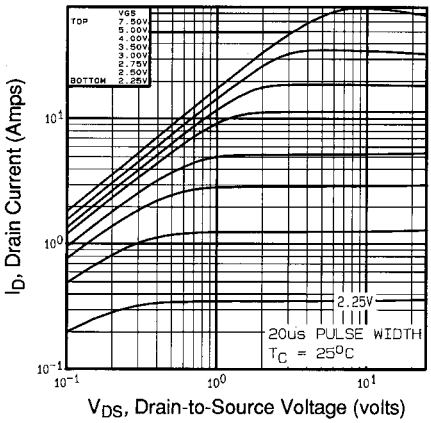



**Fig 1.** Typical Output Characteristics, $T_C$=25°C

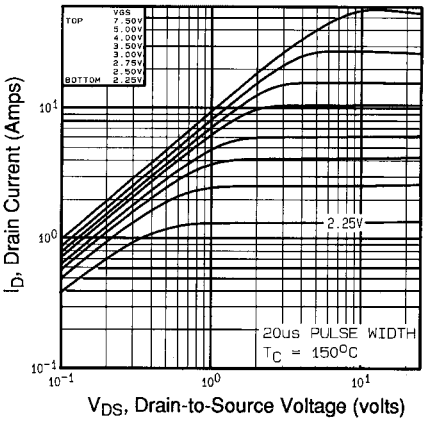



**Fig 2.** Typical Output Characteristics, $T_C$=150°C

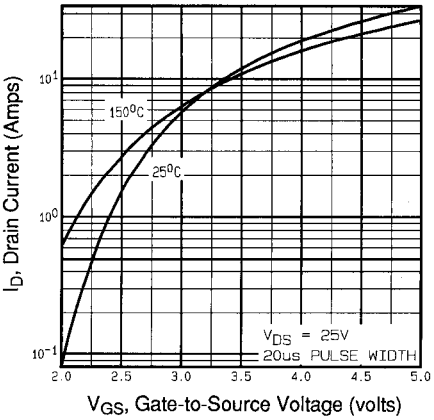



**Fig 3.** Typical Transfer Characteristics

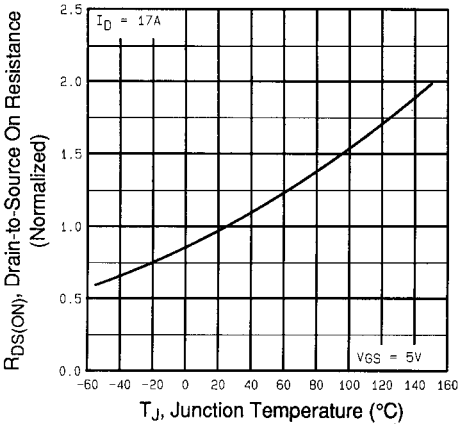



**Fig 4.** Normalized On-Resistance Vs. Temperature

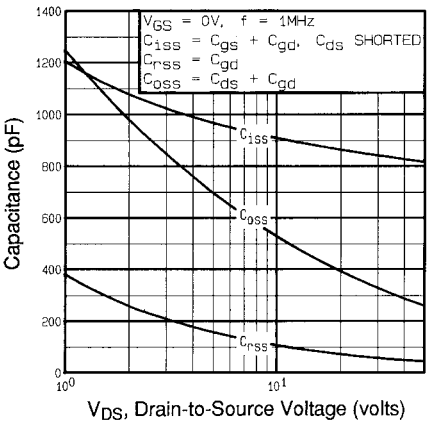



**Fig 5.** Typical Capacitance Vs. Drain-to-Source Voltage

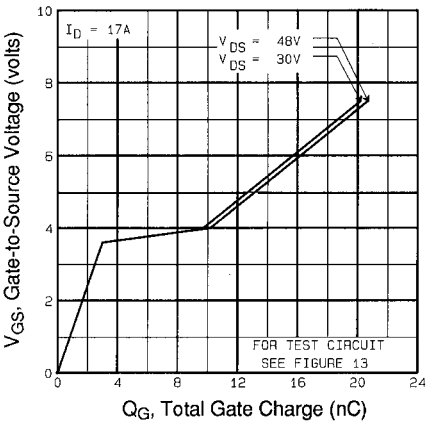



**Fig 6.** Typical Gate Charge Vs. Gate-to-Source Voltage

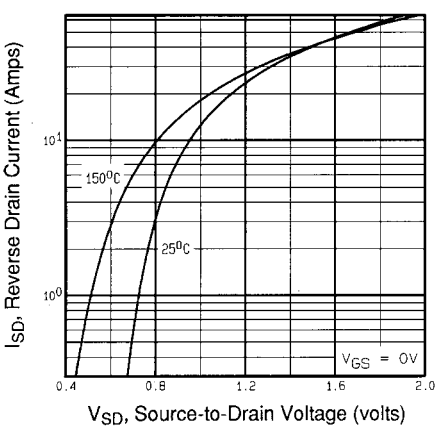



**Fig 7.** Typical Source-Drain Diode Forward Voltage

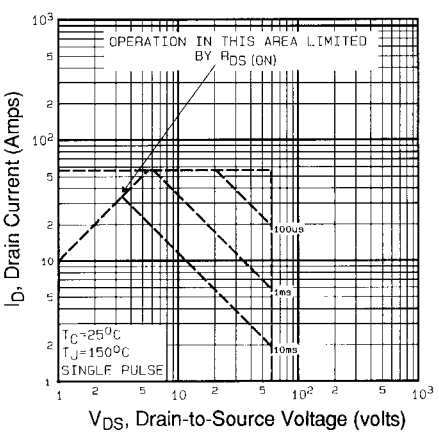



**Fig 8.** Maximum Safe Operating Area

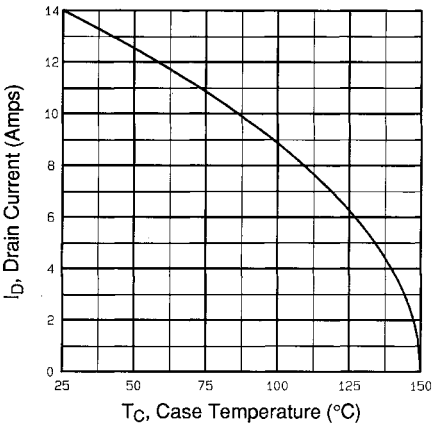



**Fig 9.** Maximum Drain Current Vs. Case Temperature

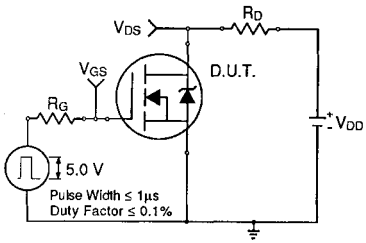



**Fig 10a.** Switching Time Test Circuit

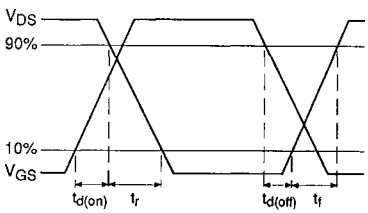



**Fig 10b.** Switching Time Waveforms

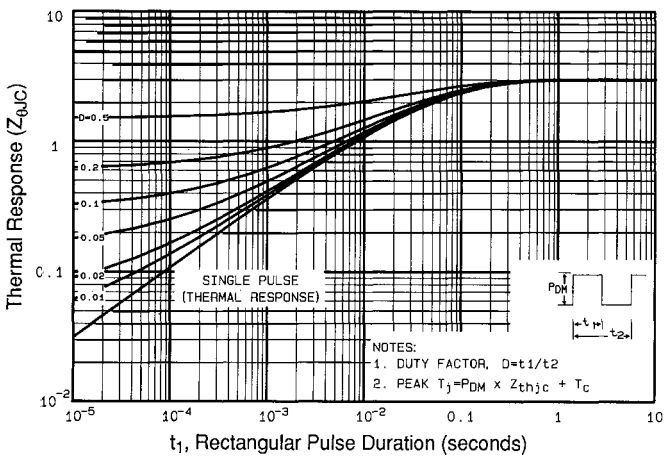



**Fig 11.** Maximum Effective Transient Thermal Impedance, Junction-to-Case

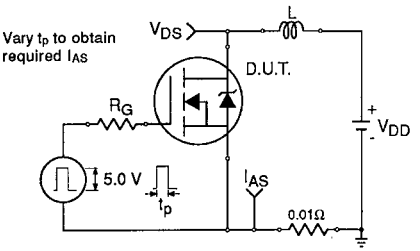



**Fig 12a.** Unclamped Inductive Test Circuit

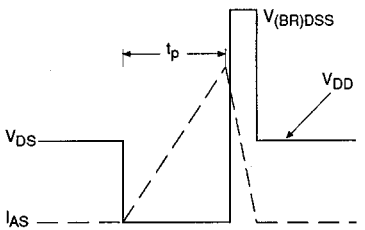



**Fig 12b.** Unclamped Inductive Waveforms

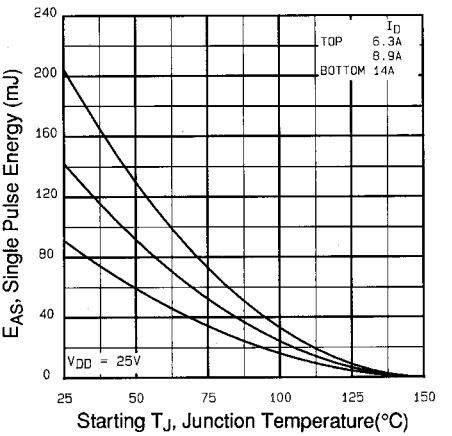



**Fig 12c.** Maximum Avalanche Energy Vs. Drain Current

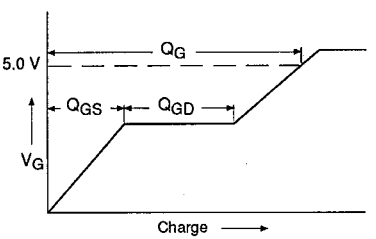



**Fig 13a.** Basic Gate Charge Waveform

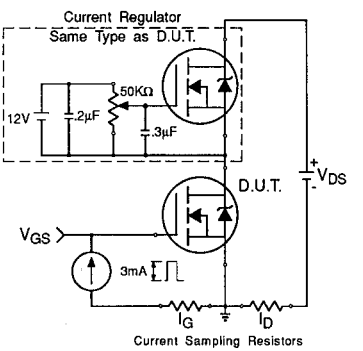



**Fig 13b.** Gate Charge Test Circuit

**Appendix A:** Figure 14, Peak Diode Recovery dv/dt Test Circuit – See page 1505

**Appendix B:** Package Outline Mechanical Drawing – See pages 1512, 1513

**Appendix C:** Part Marking Information – See page 1518

**Appendix D:** Tape & Reel Information – See page 1523